



STPS60L45CW

LOW DROP POWER SCHOTTKY RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 30 A
$T_j(\max)$	150°C
V_{RRM}	45 V
$V_F(\max)$	0.50 V

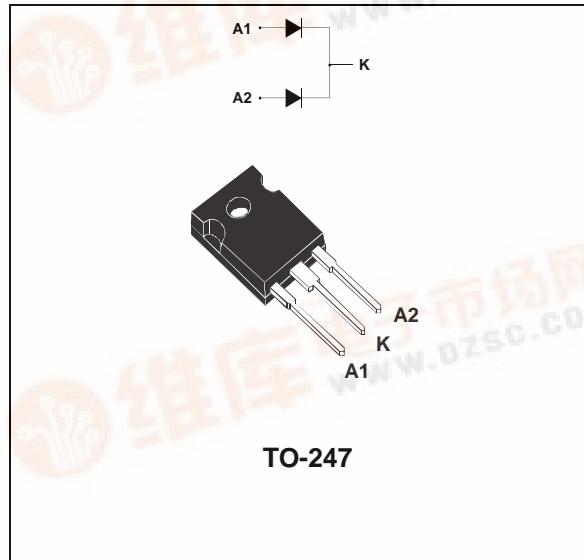
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE

DESCRIPTION

Dual center tap schottky barrier rectifier suited for 5V output in off line AC/DC power supplies.

Packaged in TO-247, this device is intended for use in low voltage, high frequency converters, free wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			45	V
$I_{F(RMS)}$	RMS forward current			50	A
$I_{F(AV)}$	Average forward current	$T_c = 135^\circ\text{C}$	Per diode Per device	30 60	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms Sinusoidal}$		600	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2 \mu\text{s square } F=1\text{kHz}$		2	A
I_{RSR}	Non repetitive peak reverse current	$t_p = 100 \mu\text{s square}$		4	A
T_{stg}	Storage temperature range				$-65 \text{ to } +150$ °C
T_j	Maximum operating junction temperature (*)				150 °C
dV/dt	Critical rate of rise of reverse voltage				10000 V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

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THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th} (j-c)	Junction to case	Per diode Total	0.75 0.42 °C/W
	Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{\text{th(j-c)}}(\text{Per diode}) + P(\text{diode 2}) \times R_{\text{th(c)}}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = 45 V			1.5	mA
		T _j = 125°C			175	350	
V _F *	Forward voltage drop	T _j = 25°C	I _F = 30 A			0.55	V
		T _j = 125°C	I _F = 30 A		0.44	0.5	
		T _j = 25°C	I _F = 60 A			0.73	
		T _j = 125°C	I _F = 60 A		0.64	0.72	

Pulse test : * tp = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation :

$$P = 0.28 \times I_{F(\text{AV})} + 0.0073 I_{F(\text{RMS})}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

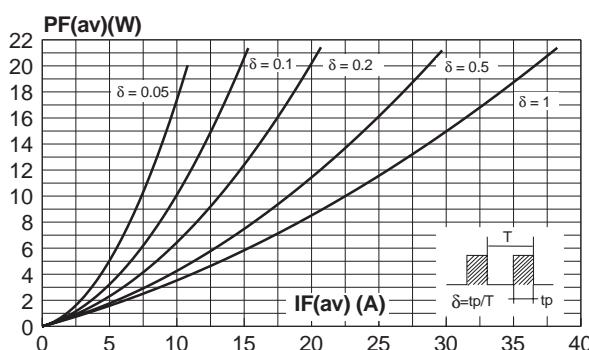


Fig. 2: Average current versus ambient temperature (δ=0.5, per diode).

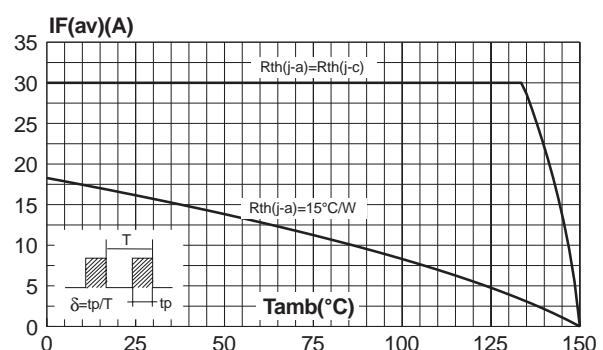


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

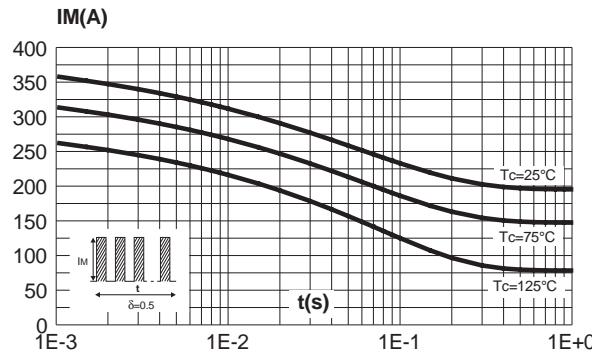


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

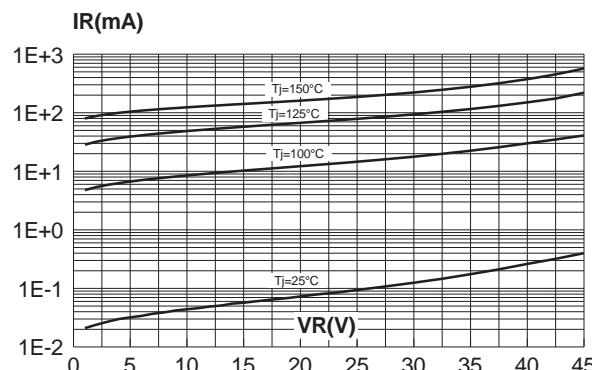


Fig. 7: Forward voltage drop versus forward current (per diode).

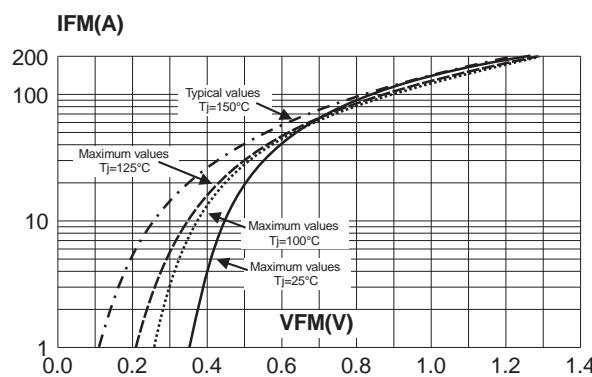


Fig. 4: Relative variation of thermal transient impedance junction to case versus pulse duration.

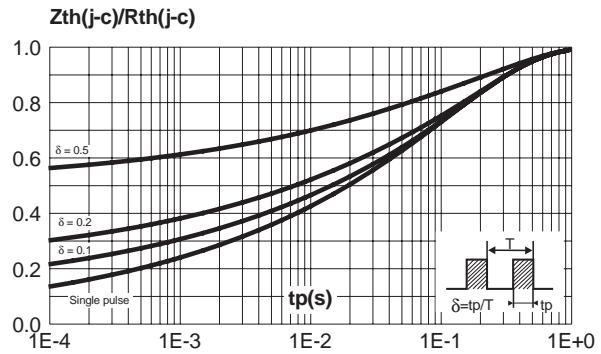
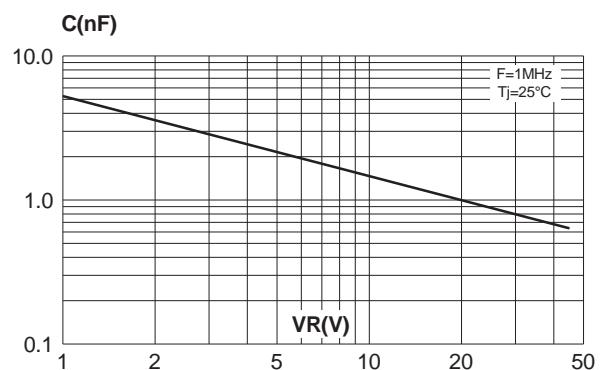
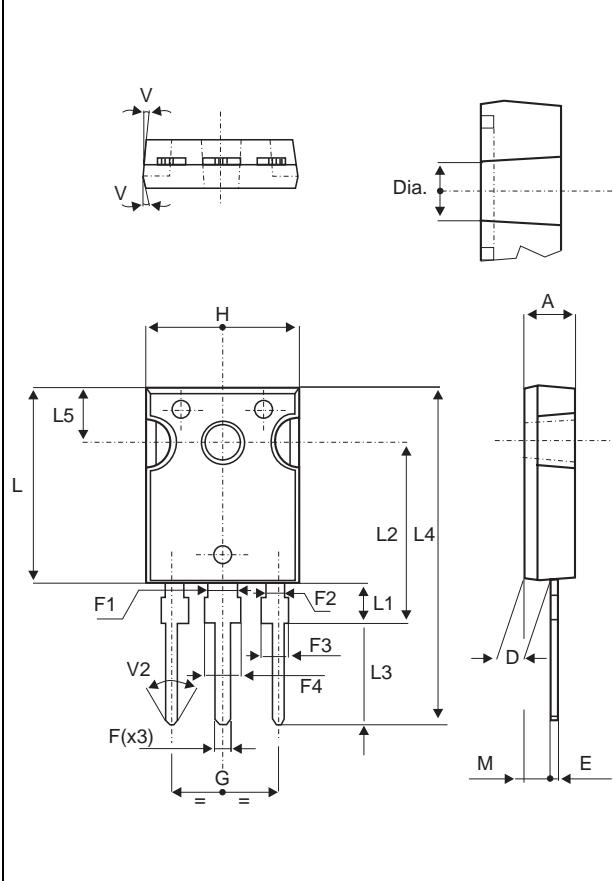


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).



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PACKAGE MECHANICAL DATA TO-247



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
E	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F1		3.00			0.118	
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
F4	3.00		3.40	0.118		0.133
G		10.90			0.429	
H	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

Type	Marking	Package	Weight	Base qty	Delivery mode
STPS60L45CW	STPS60L45CW	TO-247	4.36 g	30	Tube

- Cooling method : C
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N
- Epoxy meets UL94,V0

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